

SPTECH Silicon PNP Power Transistor

2SB1429

DESCRIPTION

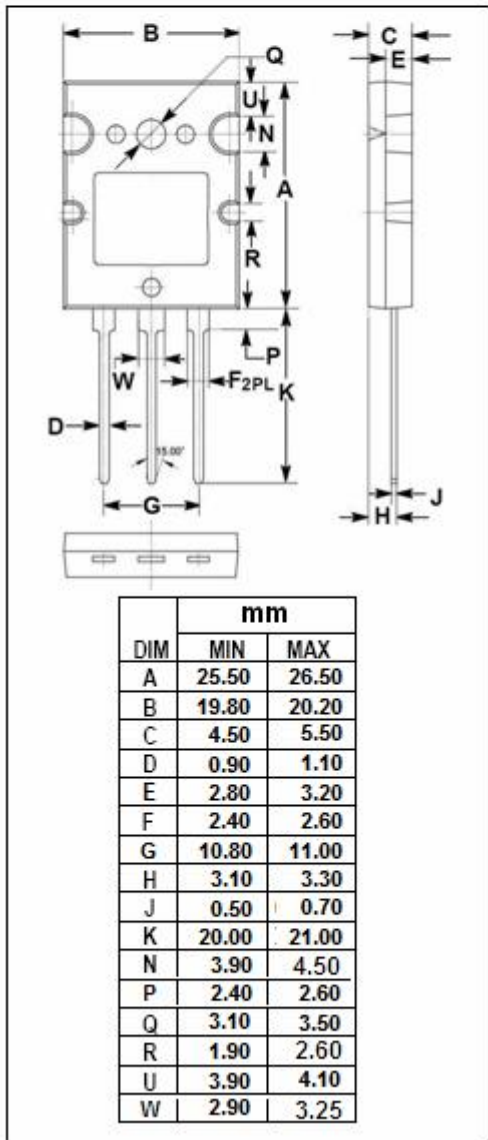
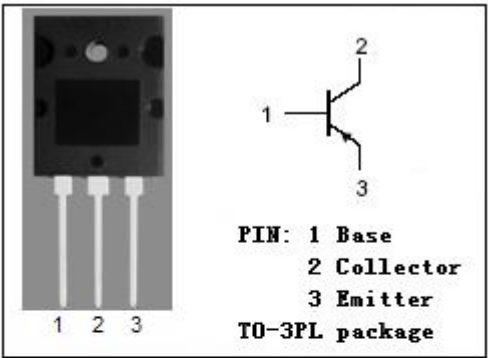
- High Current Capability
- High Power Dissipation
- Collector-Emitter Breakdown Voltage-
: $V_{(BR)CEO} = -180V(\text{Min})$
- Complement to Type 2SD2155

APPLICATIONS

- Power amplifier applications
- Recommend for 100W high fidelity audio frequency amplifier output stage applications

ABSOLUTE MAXIMUM RATINGS($T_a=25^{\circ}\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-180	V
V_{CEO}	Collector-Emitter Voltage	-180	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current-Continuous	-15	A
I_B	Base Current-Continuous	-1.5	A
P_C	Collector Power Dissipation @ $T_C=25^{\circ}\text{C}$	150	W
T_J	Junction Temperature	150	$^{\circ}\text{C}$
T_{stg}	Storage Temperature Range	-55~150	$^{\circ}\text{C}$



SPTECH Silicon PNP Power Transistor**2SB1429****ELECTRICAL CHARACTERISTICS****T_C=25°C unless otherwise specified**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	I _C = -30mA ; I _B = 0	-180			V
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = -8A; I _B = -0.8A			-3.0	V
V _{BE(on)}	Base-Emitter On Voltage	I _C = -6A ; V _{CE} = -5V			-1.5	V
I _{CBO}	Collector Cutoff Current	V _{CB} = -180V ; I _E = 0			-5	μ A
I _{EBO}	Emitter Cutoff Current	V _{EB} = -5V; I _C = 0			-5	μ A
h _{FE-1}	DC Current Gain	I _C = -1A ; V _{CE} = -5V	55		160	
h _{FE-2}	DC Current Gain	I _C = -6A ; V _{CE} = -5V	30			
C _{OB}	Output Capacitance	I _E = 0; V _{CB} = -10V; f _{test} = 1.0MHz		340		pF
f _T	Current-Gain—Bandwidth Product	I _C = -1A ; V _{CE} = -5V		10		MHz

◆ **h_{FE-1} Classifications**

R	O
55-110	80-160